NSN 5962-01-430-2121

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View Online at https://aerobasegroup.com/nsn/5962-01-430-2121

Body Length: 1.060 inches **Body Width:** Between 0.220 inches and 0.310 inches **Body Height:** Between 0.140 inches and 0.185 inches **Maximum Power Dissipation Rating:** 303.0 milliwatts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius **End Application:** Pacer dawn **Features Provided:** Hermetically sealed and burn in and programmable and bipolar and monolithic and electrostatic sensitive **Inclosure Material:** Ceramic Inclosure Configuration: Dual-in-line **Output Logic Form:** Transistor-transistor logic **Input Circuit Pattern:** 12 input **Criticality Code Justification:** Cbbl **Case Outline Source And Designator:** D-8 mil-m-38510 **Terminal Surface Treatment:** Solder **Product Name:** Microcircuit, digital, bipolar programmable array logic Voltage Rating And Type Per Characteristic: 7.0 volts power source **Time Rating Per Chacteristic:** 50.00 nanoseconds propagation delay time, low to high level output and 50.00 nanoseconds propagation delay time, high to low level output Memory Device Type: Pal **Special Features:** Altered item programmable to drwg. 90305-9 make from 5962-8851503ra

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

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Terminal Type And Quantity:

20 printed circuit

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

Fiig:

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